AMENDMENTS TO THE SPECIFICATION

Kindly replace the title of the specification as follows:

~~SEMICONDUCTOR DEVICE COMPRISING A FIELD-EFFECT TRANSISTOR AND METHOD OF OPERATING THE SAME~~ SEMICONDUCTOR TRANSISTOR (DMOS) DEVICE FOR USE AS A POWER AMPLIFIER

Kindly amend the paragraph [0028] of the published application (page 7, line 28 through page 8, line 8, of the specification as filed) as follows:

Further metal tracks 20 are provided between the polysilicide tracks 18 of the gate electrode 9 and the Al tracks 16 of the drain contact. Said tracks 20 are connected to an electrode 31 of a capacitor 30 and also to a connecting bond pad 35, where an external voltage is applied during operation of the device 10. The (partially interconnected) shielding tracks 20 are connected to the capacitor 30 at evenly spaced positions, said tracks being formed in the lower layer of the two metal layers 20,18 that are separated from each other by means of an insulating silicon dioxide layer 77. The use of a two-metal layer process makes it possible for the metal tracks [[22]] 20 to cross the gate electrode 9,18. This makes it possible to connect metal tracks 20 having a minimum resistivity. In this example, another electrode of the capacitor 30 is formed by the portion of the semiconductor body 1 that is present under a thin oxide layer 36, in this case a portion of the epitaxial layer 3 and the substrate 2, which electrode is connected to the source connection 12, therefore. The upper electrode 31 is connected, via metal plugs 34 and an additional metal layer 37 incorporated therein, to a polycrystalline silicon region 99 present on the oxide layer 36 and to the further metal strip 20. In this example, the capacity is 100 pF.